# **BLF8G24L-200P**; **BLF8G24LS-200P**

**Power LDMOS transistor** 

Rev. 1.1 — 20 February 2012

**Objective data sheet** 

# 1. Product profile

## 1.1 General description

200 W LDMOS power transistor for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{\text{case}} = 25 \, ^{\circ}\text{C}$  in a common source class-AB production test circuit.

Mode of operation	f	I <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2300 to 2400	1400	28	60	16.5	30	-38 <u>[1]</u>

<sup>[1]</sup> Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R<sub>th</sub> providing excellent thermal stability
- Designed for broadband operation (2300 MHz to 2400 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

# 1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range



# 2. Pinning information

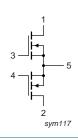
Table 2. Pinning

	•			
Pin	Description		Simplified outline	Graphic symbol
BLF8G24L-2	00P (SOT539A)			
1	drain1			
2	drain2		1 2	1
3	gate1		2	3
4	gate2		3 4	5
5	source	[1]		4
				" <u> </u>
				2 sym117
				Syllilli

#### **BLF8G24LS-200P (SOT539B)**

1	drain1	
2	drain2	
3	gate1	
4	gate2	
5	source	[1]





[1] Connected to flange.

# 3. Ordering information

Table 3. Ordering information

•						
Type number	Package					
	Name	Description	Version			
BLF8G24L-200P	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLF8G24LS-200P	-	earless flanged balanced LDMOST ceramic package; 4 leads	SOT539B			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	68	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
$I_D$	drain current		-	37	Α
$T_{stg}$	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	200	°C

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## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 60 W	<tbd></tbd>	K/W

# 6. Characteristics

Table 6. Characteristics

 $T_i = 25 \,^{\circ}\text{C}$  per section, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Tvn	Max	Unit
Syllibol	Parameter	Conditions	IVIIII	Тур	IVIAX	Unit
$V_{(BR)DSS} \\$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1 \text{ mA}$	68	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V};$ $I_{D} = 100 \text{ mA}$	1.5	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	22.8	-	-	Α
$I_{GSS}$	gate leakage current	$V_{GS}$ = 11 V; $V_{DS}$ = 0 V	-	-	280	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 5.1 \text{ A}$	-	<tbd></tbd>	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.04 \text{ A}$	0.032	-	0.166	Ω

# 7. Test information

Remark: All testing performed in a class-AB production test circuit.

#### Table 7. Functional test information

Mode of operation: 1-carrier W-CDMA, PAR = 7.2 dB at 0.01 % probability on the CCDF, 3GPP test model 1; 64 DPCH;  $f_1$  = 2300 MHz;  $f_2$  = 2400 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 1400 mA;  $T_{case}$  = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$P_{L(AV)}$	average output power		-	60	-	W
Gp	power gain		<tbd></tbd>	16.5	-	dB
RLin	input return loss		-	-10	-	dB
$\eta_{D}$	drain efficiency		<tbd></tbd>	30	-	%
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)		-	-38	<tbd></tbd>	dBc

# 7.1 Ruggedness in class-AB operation

The BLF8G24L-200P and BLF8G24LS-200P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 1400 \text{ mA}$ ;  $P_{L} = 200 \text{ W}$  (CW); f = 2300 MHz.

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# 8. Package outline

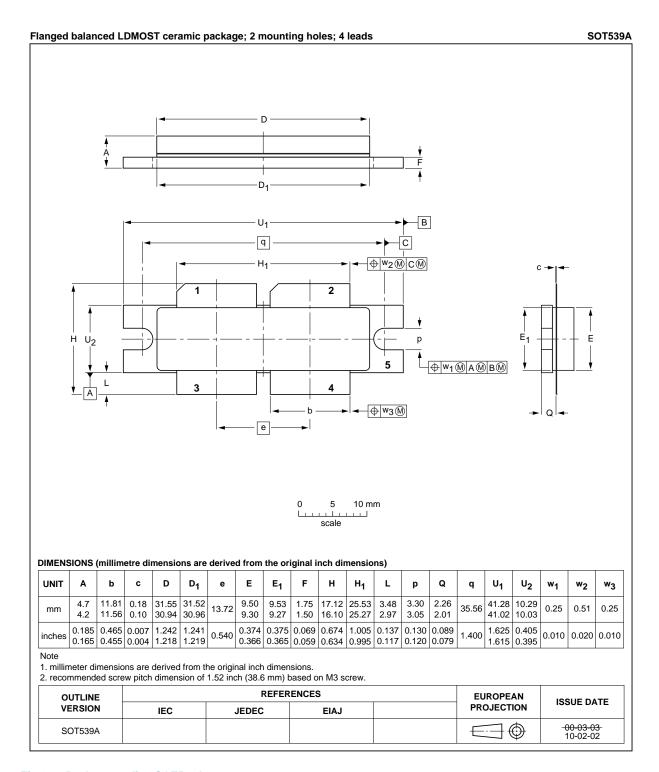


Fig 1. Package outline SOT539A

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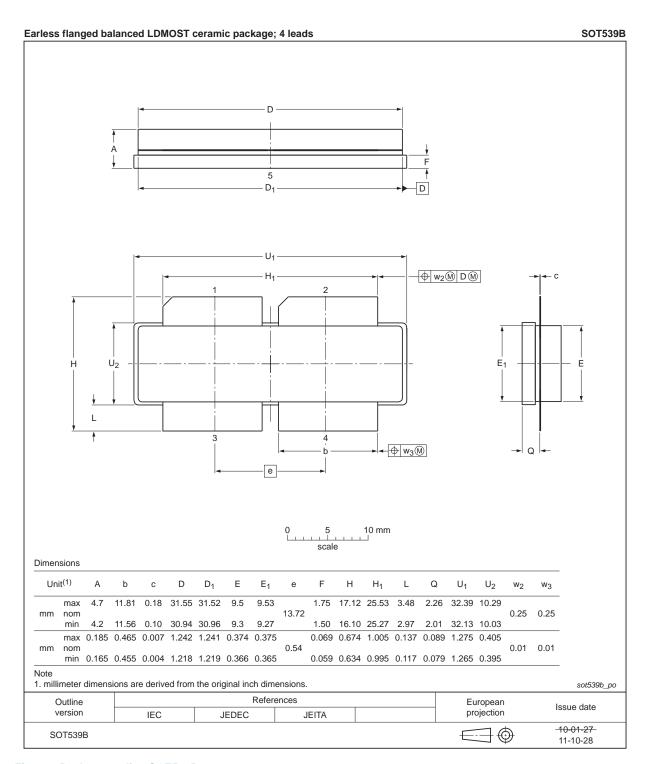


Fig 2. Package outline SOT539B

# 9. Abbreviations

Table 8. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
DPCH	Dedicated Physical Channel
CW	Continuous Wave
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

# 10. Revision history

#### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G24L-200P_8G24LS-200P v.1.1	20120220	Objective data sheet	-	-

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**Power LDMOS transistor** 

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